

N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
50V	1.8Ω @ $V_{GS} = 10V$	500mA
	2.0Ω @ $V_{GS} = 4.5V$	450mA

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

Features and Benefits

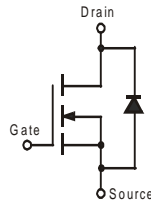
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The BSN20Q is suitable for automotive applications requiring specific change control; it is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
- <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

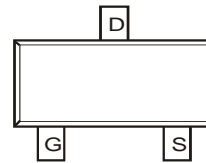
- Case: SOT23
- Case Material: Molded Plastic "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View



Equivalent Circuit



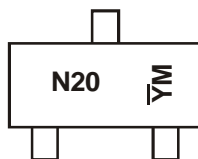
Top View

Ordering Information (Note 4)

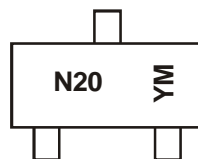
Part Number	Qualification	Case	Packaging
BSN20-7	Standard	SOT23	3000/Tape & Reel
BSN20Q-7	Automotive	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

N20 = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 ȲM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Ȳ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	50	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current @ $T_{SP} = +25^\circ\text{C}$ (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	I_D	500	mA
		$T_A = +100^\circ\text{C}$		300	
Pulsed Drain Current @ $T_{SP} = +25^\circ\text{C}$ (Notes 5 & 6)			I_{DM}	1.2	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Power Dissipation, @ $T_A = +25^\circ\text{C}$ (Note 5)	P_D	600	mW
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Power Dissipation, @ $T_{SP} = +25^\circ\text{C}$ (Note 5)	P_D	920	mW
Thermal Resistance, @ $T_{SP} = +25^\circ\text{C}$ (Note 5)	$R_{\theta JSP}$	136	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	–	–	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	–	–	0.5	μA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	–	–	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.4	1.0	1.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	–	1.3 1.6	1.8 2.0	Ω	$V_{GS} = 10V, I_D = 0.22A$ $V_{GS} = 4.5V, I_D = 0.1A$
Forward Transfer Admittance	$ Y_{fs} $	40	320	–	mS	$V_{DS} = 10V, I_D = 0.1A$
Diode Forward Voltage	V_{SD}	–	1.0	1.5	V	$V_{GS} = 0V, I_S = 180mA$
Source (diode forward) Current	I_S	–	–	194	mA	$T_{SP} = +25^\circ\text{C}$
Peak Source (diode forward) Current	I_{SM}	–	–	1.2	A	$T_{SP} = +25^\circ\text{C}$ (Note 3)
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	–	21.8	40	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	C_{oss}	–	5.6	15	pF	
Reverse Transfer Capacitance	C_{rss}	–	3.3	10	pF	
Gate Resistance	R_g	–	49	–	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	–	800	–	pC	$V_{GS} = 10V, V_{DD} = 25V,$ $I_D = 250mA$
Gate-Source Charge	Q_{gs}	–	100	–	pC	
Gate-Drain Charge	Q_{gd}	–	100	–	pC	
Turn-On Delay Time	$t_{D(on)}$	–	2.93	–	ns	$V_{DD} = 30V, V_{GEN} = 10V,$ $R_L = 150\Omega, R_{GEN} = 50\Omega,$ $I_D = 0.2A$
Turn-On Rise Time	t_r	–	2.99	–	ns	
Turn-Off Delay Time	$t_{D(off)}$	–	9.45	–	ns	
Turn-Off Fall Time	t_f	–	8.3	–	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

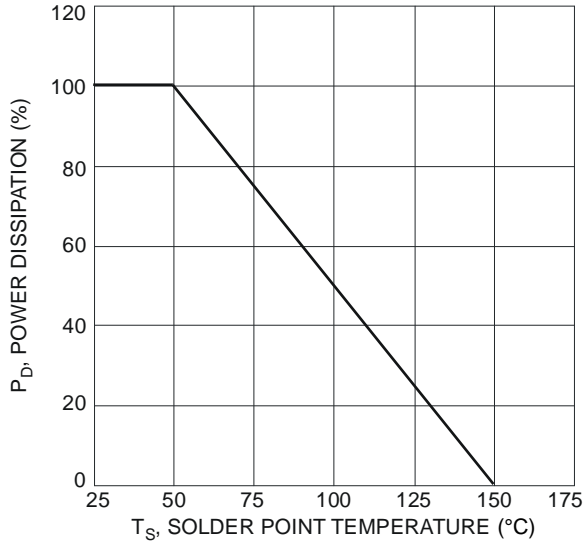


Fig 1. Normalized Total Power Dissipation as a Function of Solder Point Temperature

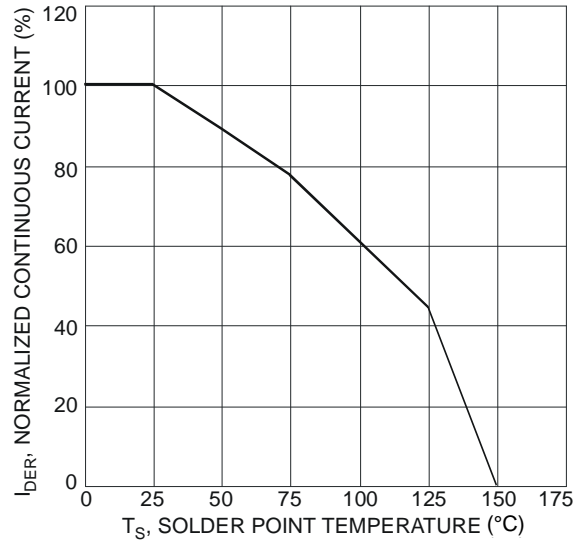


Fig 2. Normalized Continuous Current vs. Solder Point Temperature

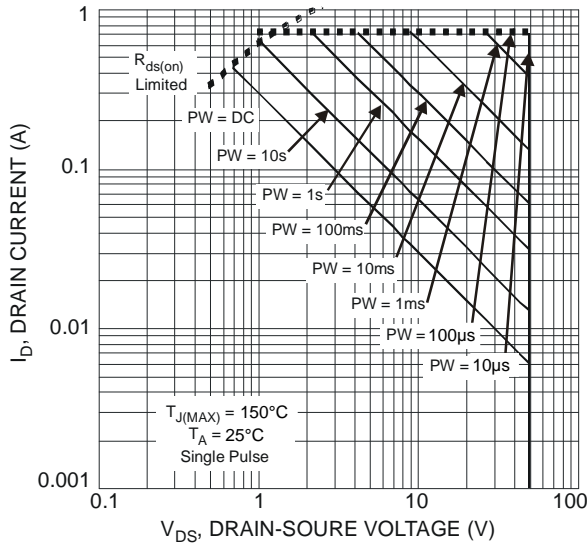


Fig 3 SOA, Safe Operation Area

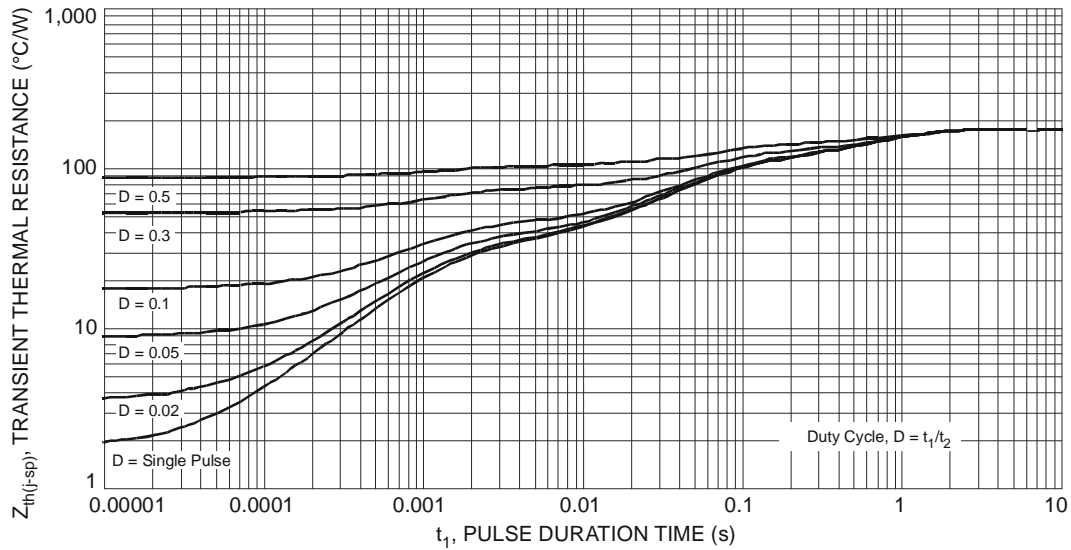


Fig 4 Transient Thermal Response

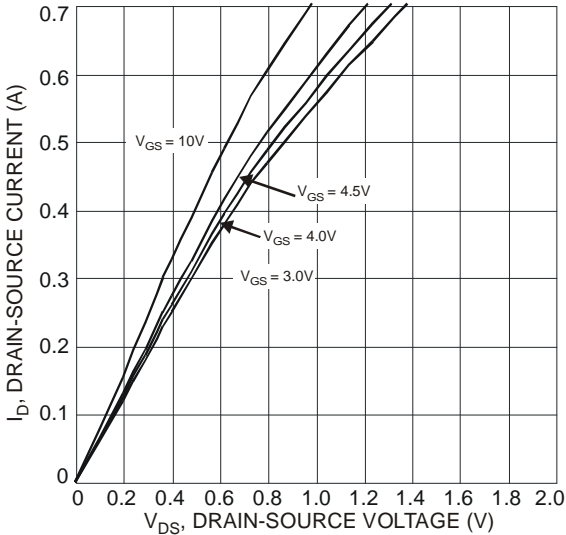


Fig. 5 Drain-Source Current vs. Drain-Source Voltage

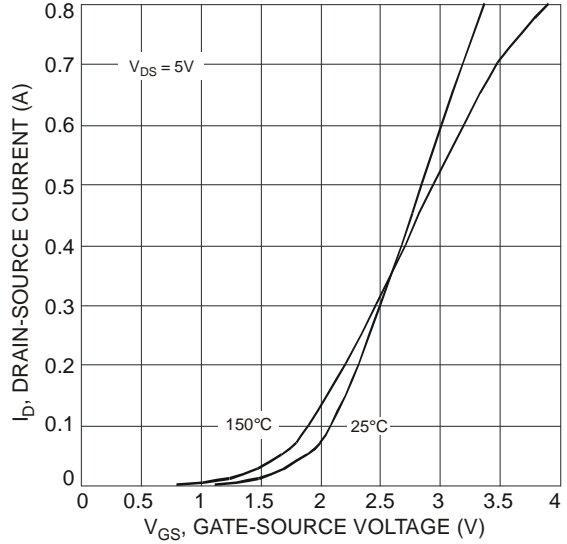


Fig. 6 Transfer Characteristics

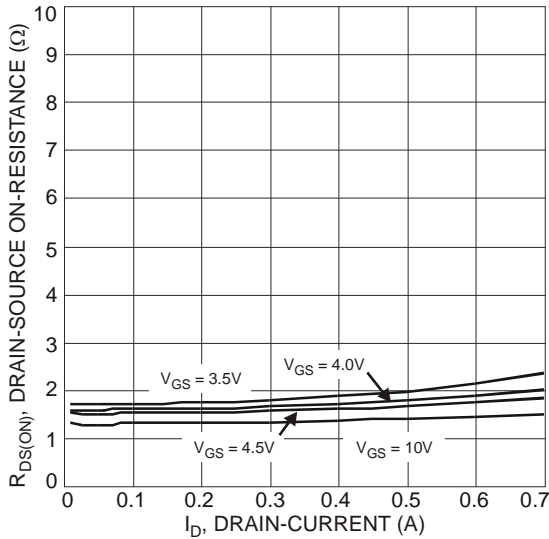


Fig. 7 Drain-Source On-Resistance vs. Drain-Current

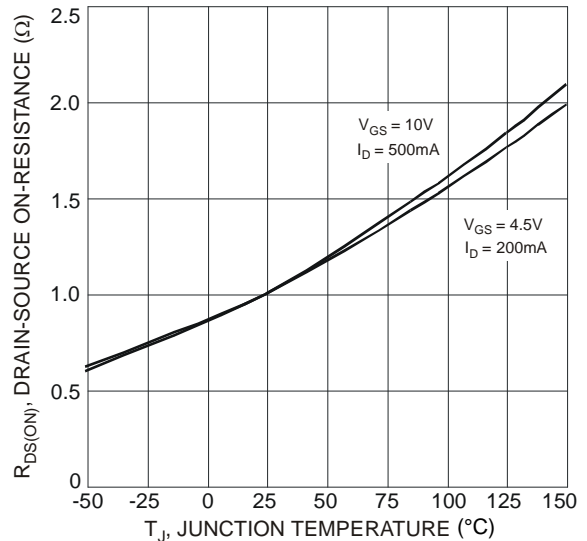


Fig. 8 Drain-Source On-Resistance vs. Junction Temperature

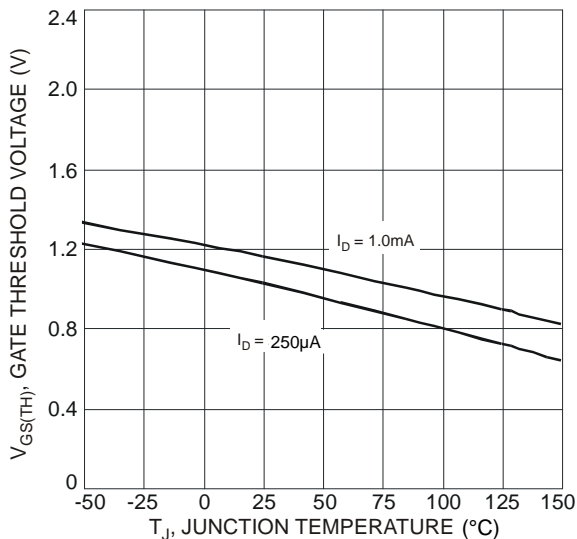


Fig. 9 Gate Threshold Voltage vs. Junction Temperature

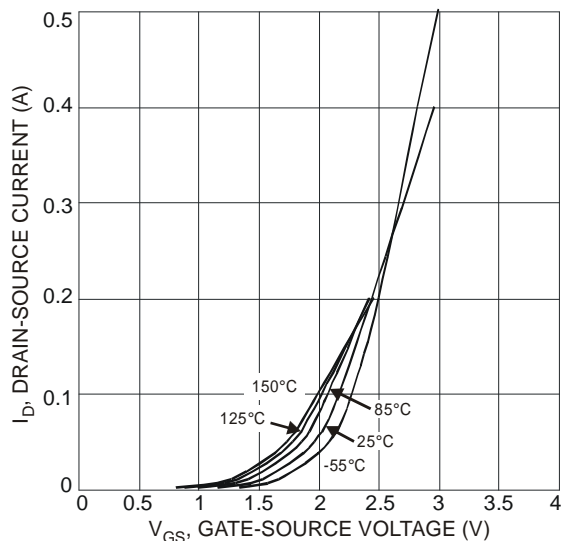


Fig. 10 Transfer Characteristics

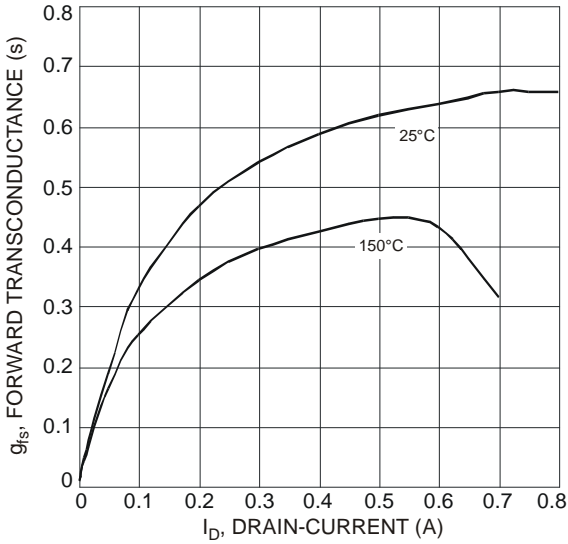


Fig. 11 Typical Transfer Characteristic

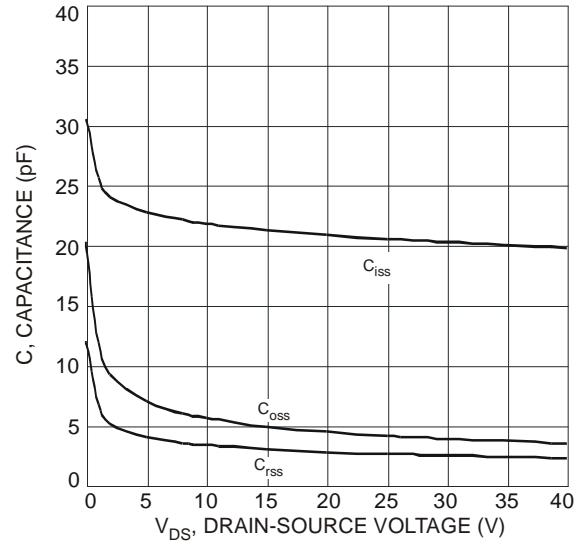


Fig. 12 Capacitance vs. Drain-Source Voltage

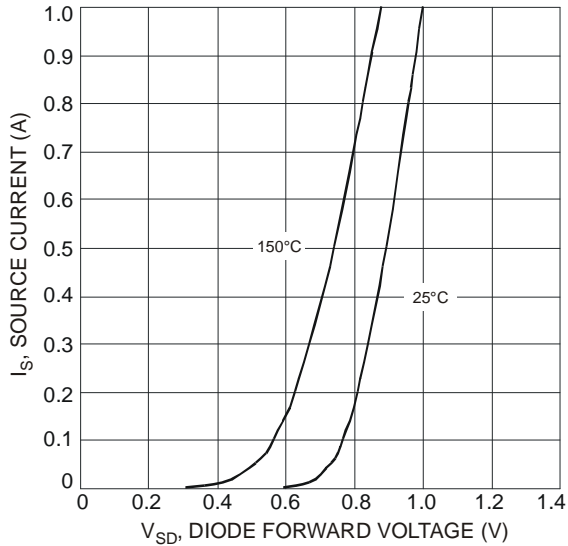
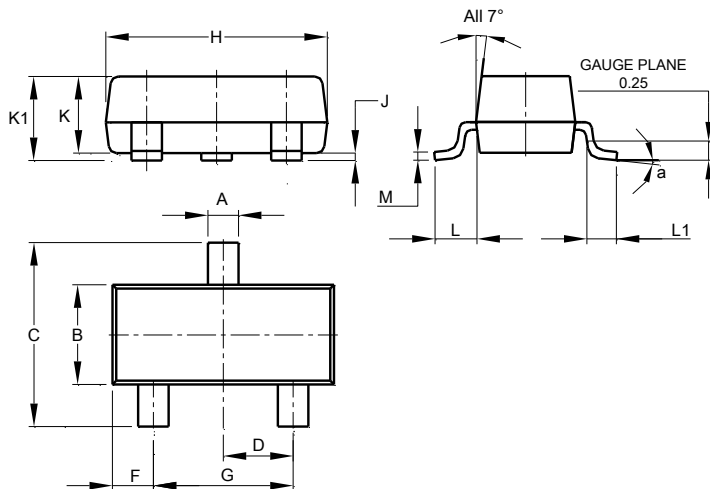


Fig. 13 Source Current vs. Diode Forward Voltage

Package Outline Dimensions

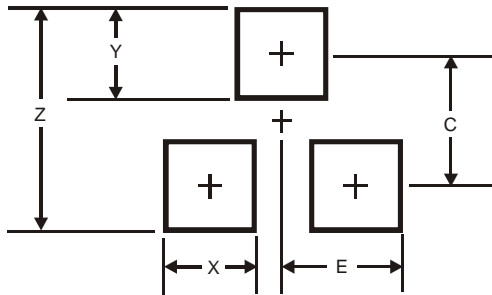
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
α	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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